



Phase Control Thyristor

DS5960-3 December 2013 (LN31164)

FEATURES

- Double Side Cooling
- High Surge Capability

APPLICATIONS

- High Power Drives
- High Voltage Power Supplies
- Static Switches

VOLTAGE RATINGS

Part and Ordering Number	Repetitive Peak Voltages V _{DRM} and V _{RRM} V	Conditions
DCR2040L42 DCR2040L40 DCR2040L35	4200 4000 3500	$\begin{split} T_{vj} = -40 ^{\circ} C \text{ to } 125 ^{\circ} C, \\ I_{DRM} = I_{RRM} = 200 \text{mA}, \\ V_{DRM}, V_{RRM} t_p = 10 \text{ms}, \\ V_{DSM} \& V_{RSM} = \\ V_{DRM} \& V_{RRM} + 100 V \\ respectively \end{split}$

Lower voltage grades available.

ORDERING INFORMATION

When ordering, select the required part number shown in the Voltage Ratings selection table.

For example:

DCR2040L42

Note: Please use the complete part number when ordering and quote this number in any future correspondence relating to your order.

KEY PARAMETERS

V_{DRM}	4200V
I _{T(AV)}	2040A
I _{TSM}	29000A
dV/dt*	1500V/µs
dl/dt	400A/μs

* Higher dV/dt selections available

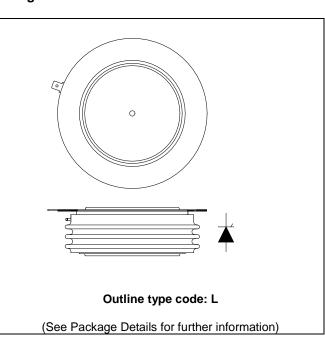


Fig. 1 Package outline





CURRENT RATINGS

T_{case} = 60°C unless stated otherwise

Symbol	Parameter	Test Conditions	Max.	Units
Double Sid	de Cooled			
I _{T(AV)}	Mean on-state current	Half wave resistive load	2040	А
I _{T(RMS)}	RMS value	-	3204	А
I _T	Continuous (direct) on-state current	-	2965	А

SURGE RATINGS

Symbol	Parameter	Test Conditions	Max.	Units
I _{TSM}	Surge (non-repetitive) on-state current	10ms half sine, T _{case} = 125°C	29	kA
l ² t	I ² t for fusing	$V_R = 0$	4.2	MA ² s

THERMAL AND MECHANICAL RATINGS

Symbol	Parameter	Test Conditions		Min.	Max.	Units
R _{th(j-c)}	Thermal resistance – junction to case	Double side cooled	DC	-	0.0117	°C/W
		Single side cooled	Anode DC	-	0.0187	°C/W
			Cathode DC	-	0.0329	°C/W
R _{th(c-h)}	Thermal resistance – case to heatsink	Clamping force 37kN	Double side	-	0.0025	°C/W
		(with mounting compound)	Single side	-	0.005	°C/W
T_{vj}	Virtual junction temperature	Blocking V _{DRM} / _{VRRM}		-	125	°C
T _{stg}	Storage temperature range			-55	125	°C
F _m	Clamping force			33.0	41.0	kN





DYNAMIC CHARACTERISTICS

Symbol	Parameter	Test Conditions		Min.	Max.	Units
I _{RRM} /I _{DRM}	Peak reverse and off-state current	At V _{RRM} /V _{DRM} , T _{case} = 125°C		-	200	mA
dV/dt	Max. linear rate of rise of off-state voltage	To 67% V_{DRM} , $T_j = 125$ °C, ga	ate open	-	1500	V/µs
dl/dt	Rate of rise of on-state current	From 67% V _{DRM} to 2x I _{T(AV)}	Repetitive 50Hz	-	200	A/µs
		Gate source 30V, 10Ω,	Non-repetitive	-	400	A/µs
		$t_r < 0.5 \mu s, T_j = 125^{\circ}C$				
V _{T(TO)}	Threshold voltage – Low level	500A to 2000A at T _{case} = 125	5°C	-	0.9	V
	Threshold voltage – High level	2000A to 7000A at T _{case} = 12	25°C	-	1.08	V
r _T	On-state slope resistance – Low level	500A to 2000A at T _{case} = 125°C		-	0.36	mΩ
	On-state slope resistance – High level	2000A to 7000A at T _{case} = 125°C		-	0.265	mΩ
t _{gd}	Delay time	$V_D = 67\% V_{DRM}$, gate source 30V, 10Ω		-	3	μs
		$t_r = 0.5 \mu s, T_j = 25^{\circ}C$				
t _q	Turn-off time	$T_j = 125$ °C, $V_R = 200$ V, $dI/dt = 1$ A/ μ s,		250	500	μs
		dV _{DR} /dt = 20V/μs linear				
Qs	Stored charge	$I_T = 2000A$, $T_j = 125$ °C, $dI/dt - 1A/\mu s$,		1000	3000	μC
IL	Latching current	$T_j = 25^{\circ}C, V_D = 5V$		-	3	А
I _H	Holding current	$T_j = 25^{\circ}C, R_{G-K} = \infty, I_{TM} = 500$	0A, I _T = 5A	-	300	mA



GATE TRIGGER CHARACTERISTICS AND RATINGS

Symbol	Parameter	Test Conditions	Max.	Units
V_{GT}	Gate trigger voltage	$V_{DRM} = 5V$, $T_{case} = 25$ °C	1.5	V
V_{GD}	Gate non-trigger voltage	At V _{DRM} , T _{case} = 125°C	0.4	V
I _{GT}	Gate trigger current	V _{DRM} = 5V, T _{case} = 25°C	350	mA
I _{GD}	Gate non-trigger current	V _{DRM} = 5V, T _{case} = 25°C	10	mA

CURVES

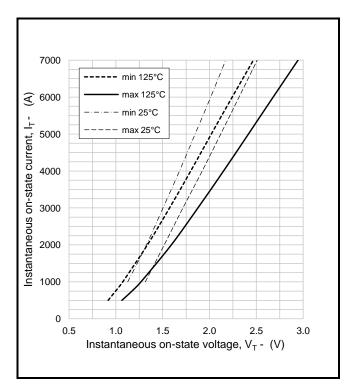


Fig.2 Maximum & minimum on-state characteristics

V_{TM} EQUATION

Where B = 0.132631

A = 0.137154

 $V_{TM} = A + Bln (I_T) + C.I_T + D.\sqrt{I_T}$

C = 0.000248

D = -0.001126

these values are valid for $T_i = 125$ °C for $I_T 100A$ to 7000A



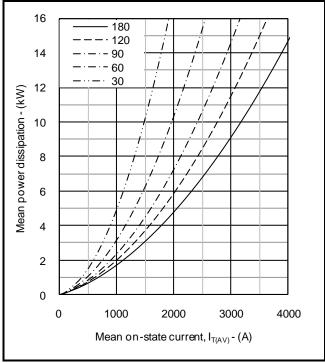


Fig.3 On-state power dissipation - sine wave

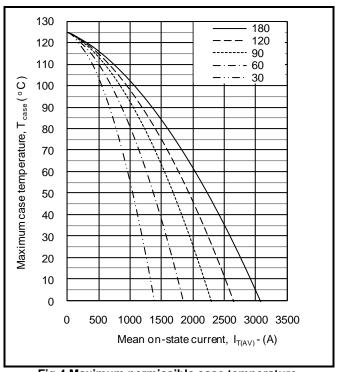


Fig.4 Maximum permissible case temperature, double side cooled – sine wave

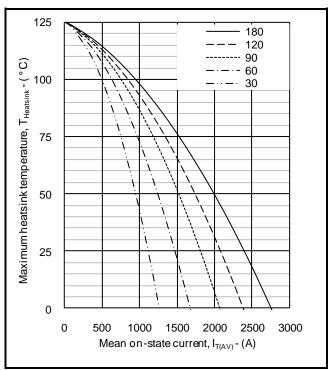


Fig.5 Maximum permissible heatsink temperature, double side cooled – sine wave

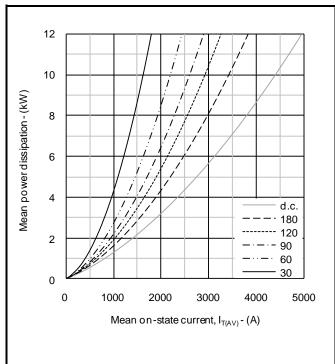


Fig.6 On-state power dissipation - rectangular wave



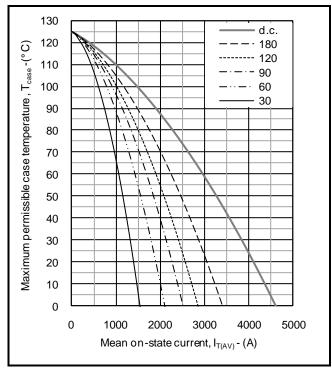


Fig.7 Maximum permissible case temperature, double side cooled – rectangular wave

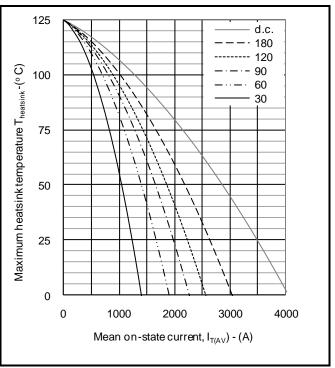
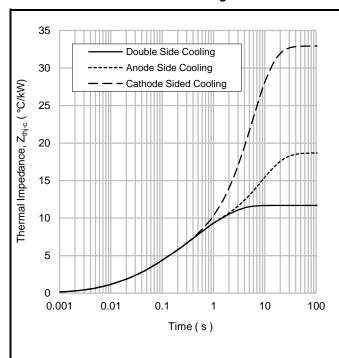


Fig.8 Maximum permissible heatsink temperature, double side cooled – rectangular wave



		1	2	3	4
Double side cooled	R _i (°C/kW)	0.8342	2.6074	4.2073	4.041
	T _i (s)	0.008639	0.0533503	0.3309504	1.612
Anode side cooled	R _i (°C/kW)	0.9647	2.8312	4.9433	9.909
	T _i (s)	0.0096096	0.0627037	0.4198958	8.908
Cathode side cooled	R _i (°C/kW)	0.9285	2.9366	2.3581	26.683
	T: (s)	0.0003033	0.0621535	0.3002235	5 835

$$Z_{th} = \sum [R_i x (1-exp. (t/t_i))]$$

 $\Delta R_{th(j-c)}$ Conduction

Tables show the increments of thermal resistance $R_{\text{th}(j\!-\!c)}$ when the device operates at conduction angles other than d.c.

Double side cooling					
	ΔZ_{th} ((z)			
θ°	sine.	rect.			
180	1.45	0.98			
120	1.68	1.40			
90	1.93	1.64			
60	2.16	1.90			
30	2.34	2.19			

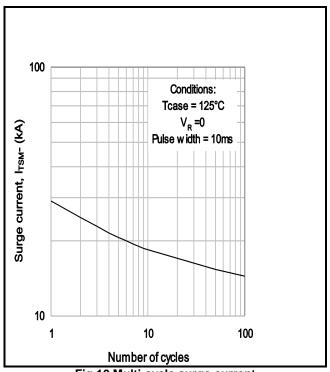
	Ariode Side	Cooling	
	ΔZ_{th} (z)		
θ°	sine.	rect.	
180	1.43	0.97	
120	1.66	1.39	
90	1.90	1.62	
60	2.12	1.88	
30	2.30	2.15	
15	2 27	2.20	

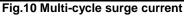
Anode Side Cooling

Cathode Sided Cooling				
	$\Delta Z_{th}(z)$			
θ°	sine.	rect.		
180	1.44	0.97		
120	1.66	1.39		
90	1.91	1.63		
60	2.14	1.89		
30	2.31	2.17		
15	2 30	2 31		

Fig.9 Maximum (limit) transient thermal impedance - junction to case (°C/kW)







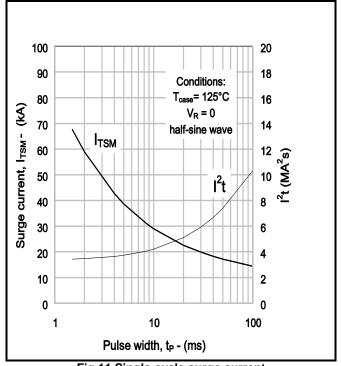


Fig.11 Single-cycle surge current

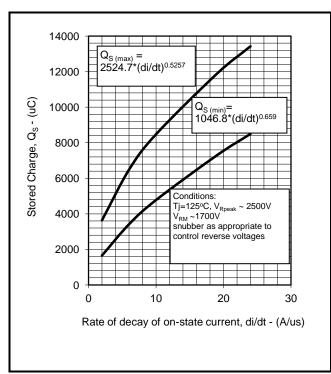


Fig.12 Reverse recovery charge

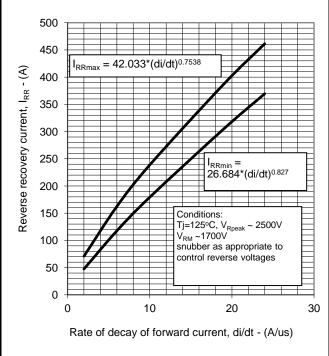


Fig.13 Reverse recovery current

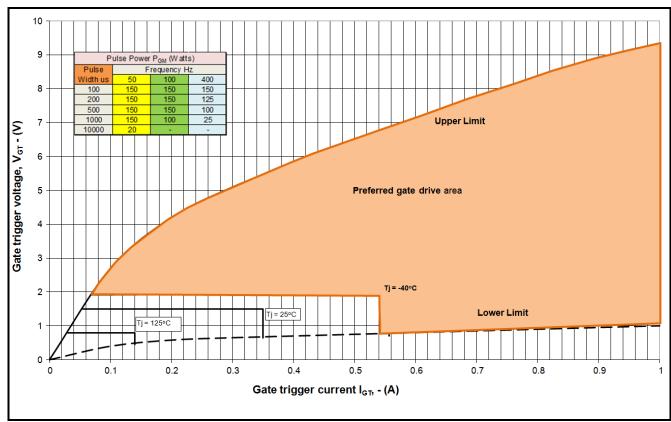


Fig14 Gate Characteristics

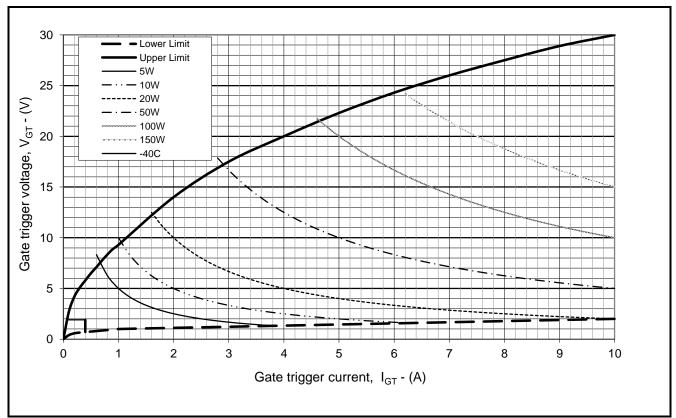


Fig. 15 Gate characteristics





PACKAGE DETAILS

For further package information, please contact Customer Services. All dimensions in mm, unless stated otherwise. DO NOT SCALE.

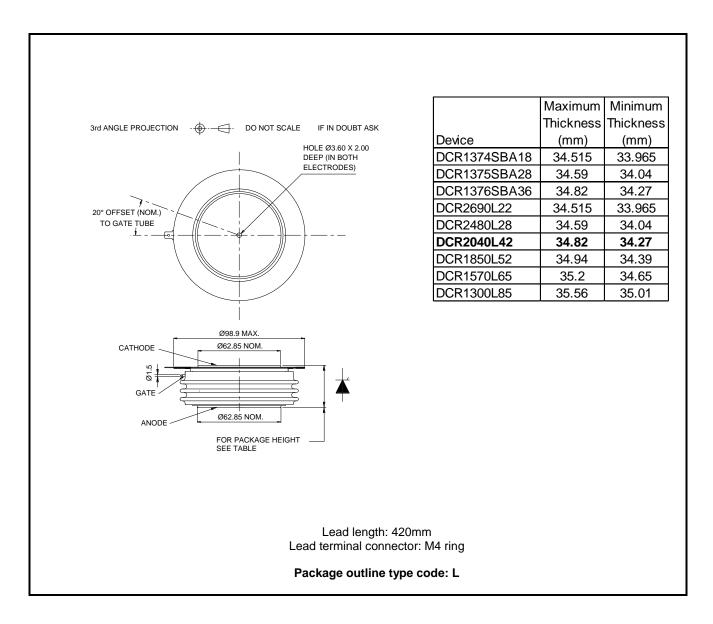


Fig.16 Package outline





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